



IN THE CLAIMS:

(Currently Amended) A semiconductor testing circuit for performing a test of a semiconductor storage device, comprising:

a plurality of counters which designate a plurality of different portions of an address signal used in at least one of a write operation and a read operation of the semiconductor storage device, said at least one of a write operation and a read operation comprising the test of the semiconductor storage device, each of the plurality of different portions comprising one bit or a plurality of successive bits; and

a switching circuit which selectively outputs counter-control signals for individually controlling operations of said plurality of counters, where each of said counter-control signals is one of a common counter-control signal commonly used for said plurality of counters and the most significant bit of one of said plurality of portions outputted from a first one of said plurality of counters other than a second one of said plurality of counters for which said each of said counter-control signals is outputted.

2. (Original) The semiconductor testing circuit according to claim 1, wherein said switching circuit outputs said common counter-control signal to one of said plurality of counters, and said most significant bit to each of another or others of said plurality of counters.

3. (Original) The semiconductor testing circuit according to claim 1, wherein said switching circuit comprises a plurality of individual switching circuits which are respectively provided in correspondence with said plurality of counters, and said counter-control signals are outputted from the plurality of individual switching circuits corresponding to said plurality of counters, respectively.

4. (Original) The semiconductor testing circuit according to claim 1, wherein a first one of said plurality of counters designates a column address of said semiconductor storage device, and a second one of said plurality of counters designates a row address of said semiconductor storage device.

5. (Original) The semiconductor testing circuit according to claim 4, wherein said first one of said plurality of counters is realized by a synchronous counter, and said second one of said plurality of counters is realized by an asynchronous counter.

6. (Original) The semiconductor testing circuit according to claim 4, wherein a third one of said plurality of counters designates a bank address of said semiconductor storage device.

7. (Original) The semiconductor testing circuit according to claim 1, wherein one of said plurality of counters comprises,

an asynchronous counter,

a synchronous counter having an output the most significant bit of which is inputted into said switching circuit, and

a counter selection circuit which receives one of said counter-control signals outputted for said one of said plurality of counters, selectively outputs the received one of the counter-control signals to one of said asynchronous counter and said synchronous counter, selectively receives a count value outputted from said one of the asynchronous counter and the synchronous counter, and outputs the received count value as one of said plurality of portions designated by said one of said plurality of counters.

8. (Original) The semiconductor testing circuit according to claim 7, wherein said counter selection circuit selects said synchronous counter as a destination to which the counter selection circuit outputs the received one of the counter-control signals and a source from which the counter selection circuit receives said count value, when said at least one of the write operation and the read operation is performed.

9. (Original) The semiconductor testing circuit according to claim 7, wherein said one of the plurality of portions designated by said one of said plurality of counters designates a bank address of said semiconductor storage device.

10. (Previously Presented) A semiconductor chip comprising:

a semiconductor storage device; and

a self-testing circuit for performing a test of a semiconductor storage device;

said self-testing circuit includes,

a plurality of counters which designate a plurality of different portions of an address signal used in at least one of a write operation and a read operation of the semiconductor storage device, each of the plurality of different portions comprising one bit or a plurality of successive bits, and

a switching circuit which selectively outputs counter-control signals for individually controlling operations of said plurality of counters, where each of said counter-control signals is one of a common counter-control signal commonly used for said plurality of counters and the most significant bit of one of said plurality of portions outputted from a first one of said plurality of counters other than a second one of said plurality of counters for which said each of said counter-control signals is outputted.

11. (Previously Presented) A packaged semiconductor device comprising:

a semiconductor storage device;

a self-testing circuit which performs a test of a semiconductor storage device;

and

a package in which said semiconductor storage device and said self-testing circuit are packed;

said self-testing circuit includes,

a plurality of counters which designate a plurality of different portions of an address signal used in at least one of a write operation and a read operation of the semiconductor storage device, each of the plurality of portions comprising one bit or a plurality of successive bits, and

a switching circuit which selectively outputs counter-control signals for individually controlling operations of said plurality of counters, where each of said counter-control signals is one of a common counter-control signal commonly used for said plurality of counters and the most significant bit of one of said plurality of portions outputted from a first one of said plurality of counters other than a second one of said plurality of counters for which said each of said counter-control signals is outputted.

12. (Previously Presented) A semiconductor storage device comprising:

memory cells; and

a self-testing circuit which performs a test of said memory cells;

said self-testing circuit includes,

a plurality of counters which designate a plurality of portions of an address signal used in at least one of a write operation and a read operation of the semiconductor storage device, by count values outputted from the plurality of counters, respectively,

where each of the plurality of portions is comprised of one bit or a plurality of successive bits, and

a switching circuit which selectively outputs counter-control signals for individually controlling operations of said plurality of counters, where each of said counter-control signals is one of a common counter-control signal commonly used for said plurality of counters and the most significant bit of one of said plurality of portions outputted from a first one of said plurality of counters other than a second one of said plurality of counters for which said each of said counter-control signals is outputted.

13. (Original) The semiconductor storage device according to claim 12, wherein said switching circuit outputs said common counter-control signal to one of said plurality of counters, and said most significant bit to each of another or others of said plurality of counters.

14. (Original) The semiconductor storage device according to claim 12, wherein said memory cells are arranged in a plurality of banks, which can be designated by said address signal, and the plurality of banks share a data bus through which data are written in or read from said memory cells.

15. (Currently Amended) A semiconductor testing method for performing a test of a semiconductor storage device, comprising the steps of:

(a) selectively inputting counter-control signals into a plurality of counters so as to individually control counting operations of the plurality of counters, where each of the counter-control signals is one of the most significant bit of an output of a first one of the plurality of counters other than a second one of the plurality of counters to which said each of the counter-control signals is inputted and a common counter-control signal

which is commonly used for said plurality of counters; and

(b) designating one bit or a plurality of successive bits constituting an address signal used in at least one of a write operation and a read operation of the semiconductor storage device, said at least one of a write operation and a read operation comprising the test of the semiconductor storage device, by each of count values outputted from the plurality of counters.

16. (Original) The semiconductor testing method according to claim 15, wherein said common counter-control signal is inputted into one of said plurality of counters, and said most significant bit is inputted into each of another or others of said plurality of counters.

17. (Original) The semiconductor testing method according to claim 15, wherein a column address is designated by a count value outputted from one of the plurality of counters to which said common counter-control signal is inputted, so as to perform said at least one of the write operation and the read operation in a page mode.

18. (Original) The semiconductor testing method according to claim 15, wherein a bank address is designated by a count value outputted from one of the plurality of counters to which said common counter-control signal is inputted, so as to perform said at least one of the write operation and the read operation in a bank-interleave mode.